- **Controlled Baseline** - One Assembly/Test Site, One Fabrication Site
- **Extended Temperature Performance of** –55°C to 125°C
- Enhanced Diminishing Manufacturing Sources (DMS) Support
- **Enhanced Product-Change Notification**
- **Qualification Pedigree[†]**
- **Dual Output Voltages for Split-Supply** Applications
- Selectable Power Up Sequencing for DSP Applications (See TPS704xx for Independent Enabling of Each Output)
- Output Current Range of 1 A on Regulator 1 and 2 A on Regulator 2
- **Fast Transient Response**

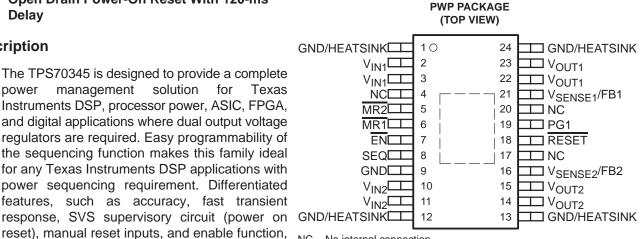
description

Output Voltages of 3.3–V/1.2–V

provide a complete system solution.

Open Drain Power-On Reset With 120-ms Delay

- **Open Drain Power Good for Regulator 1**
- Ultralow 185 µA (typ) Quiescent Current
- 2 µA Input Current During Standby
- Low Noise: 78 µV_{RMS} Without Bypass Capacitor
- **Quick Output Capacitor Discharge Feature**
- **Two Manual Reset Inputs**
- 2% Accuracy Over Load and Temperature
- Undervoltage Lockout (UVLO) Feature
- 24-Pin PowerPAD[™] TSSOP Package
- **Thermal Shutdown Protection**
- [†] Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.



NC - No internal connection



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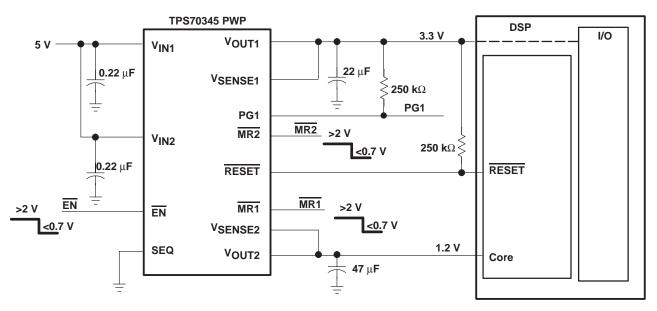
PowerPAD is a trademark of Texas Instruments.

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description (continued)



The TPS70345 voltage regulator offers low dropout voltage and dual outputs with power up sequence control, which is designed primarily for DSP applications. This device has a low noise output performance without using any added filter bypass capacitors and are designed to have a fast transient response and be stable with 47 μ F low ESR capacitors.

This device has a fixed output voltage 3.3 V/1.2 V. Regulator 1 can support up to 1 A, and regulator 2 can support up to 2 A. Separate voltage inputs allow the designer to configure the source power.

Because the PMOS pass element behaves as a low-value resistor, the dropout voltage is very low (typically 160 mV on regulator 1) and is directly proportional to the output current. Additionally, since the PMOS pass element is a voltage-driven device, the quiescent current is low and independent of output loading (maximum of 250 μ A over the full range of output current). This LDO family also features a sleep mode; applying a high signal to \overline{EN} (enable) shuts down both regulators, reducing the input current to 1 μ A at T_J = 25°C.

The device is enabled when the $\overline{\text{EN}}$ pin is connected to a low-level input voltage. The output voltages of the two regulators are sensed at the V_{SENSE1} and V_{SENSE2} pins respectively.

The input signal at the SEQ pin controls the power-up sequence of the two regulators. When the device is enabled and the SEQ terminal is pulled high or left open, V_{OUT2} turns on first and V_{OUT1} remains off until V_{OUT2} reaches approximately 83% of its regulated output voltage. At that time V_{OUT1} is turned on. If V_{OUT2} is pulled below 83% (i.e. overload condition) of its regulated voltage, V_{OUT1} will be turned off. Pulling the SEQ terminal low reverses the power-up order and V_{OUT1} is turned on first. The SEQ pin is connected to an internal pullup current source.

For each regulator, there is an internal discharge transistor to discharge the output capacitor when the regulator is turned off (disabled).

The PG1 pin reports the voltage conditions at V_{OUT1} . The PG1 pin can be used to implement a SVS (power on reset) for the circuitry supplied by regulator 1.



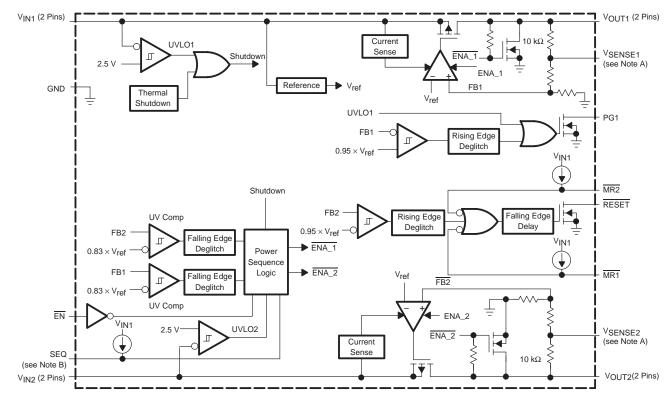
description (continued)

The TPS70345 features a RESET (SVS, POR, or power on reset). RESET is an active low, open drain output and requires a pullup resistor for normal operation. When pulled up, RESET goes to a high impedance state (i.e. logic high) after a 120 ms delay when all three of the following conditions are met. First, V_{IN1} must be above the undervoltage condition. Second, the manual reset (MR) pin must be in a high impedance state. Third, V_{OUT2} must be above approximately 95% of its regulated voltage. To monitor V_{OUT1} , the PG1 output pin can be connected to MR1 or MR2. RESET can be used to drive power on reset or a low-battery indicator. If RESET is not used, it can be left floating.

Internal bias voltages are powered by V_{IN1} and require 2.7 V for full functionality. Each regulator input has an undervoltage lockout circuit that prevents each output from turning on until the respective input reaches 2.5 V.

| AVAILABLE OPTIONS | | | | | | | | |
|-------------------|-----------------------------------|-----------------------------------|-----------------|--|--|--|--|--|
| TJ | REGULATOR 1 V _O (V) | REGULATOR 2 V _O (V) | TSSOP (PWP) | | | | | |
| -55°C to 125°C | 3.3 V | 1.2 V | TPS70345MPWPREP | | | | | |

detailed block diagram - fixed voltage version

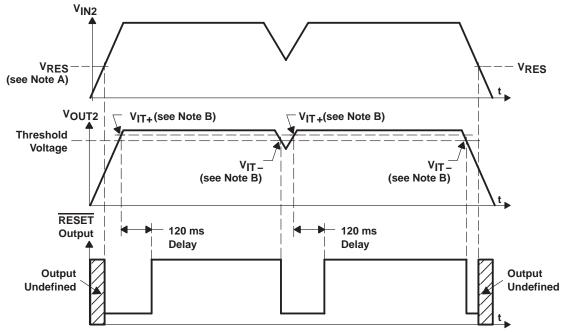


 NOTES: A. For most applications, V_{SENSE1} and V_{SENSE2} should be externally connected to V_{OUT} as close as possible to the device. For other implementations, refer to SENSE terminal connection discussion in the Application Information section.
 B. If the SEQ terminal is floating at the input, V_{OUT2} powers up first.



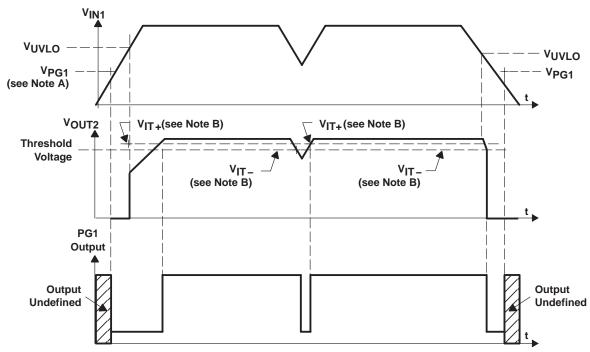
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RESET timing diagram (with V_{IN1} powered up and MR1 and MR2 at logic high)



- NOTES: A. V_{RES} is the minimum input voltage for a valid RESET. The symbol V_{RES} is not currently listed within EIA or JEDEC standards for semiconductor symbology.
 - B. VIT Trip voltage is typically 5% lower than the output voltage (95%VO) VIT– to VIT+ is the hysteresis voltage.

PG1 timing diagram



NOTES: A. VPG is the minimum input voltage for a valid PG. The symbol VPG is not currently listed within EIA or JEDEC standards for semiconductor symbology.

B. VIT –Trip voltage is typically 5% lower than the output voltage (95%VO) VIT– to VIT+ is the hysteresis voltage.



Terminal Functions

| TERMIN | NAL | | |
|--------------|---------------|-----|--|
| NAME | NO. | 1/0 | DESCRIPTION |
| EN | 7 | I | Active low enable |
| GND | 9 | | Regulator ground |
| GND/HEATSINK | 1, 12, 13, 24 | | Ground/heatsink |
| MR1 | 6 | Ι | Manual reset input 1, active low, pulled up internally |
| MR2 | 5 | Ι | Manual reset input 2, active low, pulled up internally |
| NC | 4, 17, 20 | | No connection |
| PG1 | 19 | 0 | Open drain output, low when V_{OUT1} voltage is less than 95% of the nominal regulated voltage |
| RESET | 18 | 0 | Open drain output, SVS (power on reset) signal, active low |
| SEQ | 8 | I | Power up sequence control: SEQ=High, V _{OUT2} powers up first; SEQ=Low, V _{OUT1} powers up first, SEQ terminal pulled up internally. |
| VIN1 | 2, 3 | Ι | Input voltage of regulator 1 |
| VIN2 | 10, 11 | I | Input voltage of regulator 2 |
| VOUT1 | 22, 23 | 0 | Output voltage of regulator 1 |
| VOUT2 | 14, 15 | 0 | Output voltage of regulator 2 |
| VSENSE2 | 16 | Ι | Regulator 2 output voltage sense |
| VSENSE1 | 21 | Ι | Regulator 1 output voltage sense |

detailed description

The TPS70345 low dropout regulator provides dual regulated output voltages for DSP applications that require a high performance power management solution. These devices provide fast transient response and high accuracy, while drawing low quiescent current. Programmable sequencing provides a power solution for DSPs without any external component requirements. This reduces the component cost and board space while increasing total system reliability. The TPS70345 has an enable feature which puts the device in sleep mode reducing the input current to 1 μ A. Other features are the integrated SVS (power on reset, RESET) and power good (PG1). These monitor output voltages and provide logic output to the system. These differentiated features provide a complete DSP power solution.

The TPS70345, unlike many other LDOs, features low quiescent current which remains virtually constant even with varying loads. Conventional LDO regulators use a PNP pass element, the base current of which is directly proportional to the load current through the regulator ($I_B = I_C/\beta$). The TPS70345 uses a PMOS transistor to pass current. Because the gate of the PMOS is voltage driven, operating current is low and stable over the full load range.

pin functions

enable

The \overline{EN} terminal is an input which enables or shuts down the device. If \overline{EN} is at a logic high signal the device is in shutdown mode. When the \overline{EN} goes to voltage low, then the device is enabled.

sequence

The SEQ terminal is an input that programs which output voltage (V_{OUT1} or V_{OUT2}) is turned on first. When the device is enabled and the SEQ terminal is pulled high or left open, V_{OUT2} turns on first and V_{OUT1} remains off until V_{OUT2} reaches approximately 83% of its regulated output voltage. If V_{OUT2} is pulled below 83% (i.e., over load condition) V_{OUT1} is turned off. This terminal has a 6-µA pullup current to V_{IN1} .

Pulling the SEQ terminal low reverses the power-up order and V_{OUT1} is turned on first. For detailed timing diagrams see Figure 26 through Figure 30.



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detailed description (continued)

power good (PG1)

The PG1 terminal is an open drain, active high output terminal which indicates the status of the V_{OUT1} regulator. When the V_{OUT1} reaches 95% of its regulated voltage, PG1 goes to a high impedance state. PG1 goes to a low impedance state when V_{OUT1} is pulled below 95% (i.e., over load condition) of its regulated voltage. The open drain output of the PG1 terminal requires a pullup resistor.

manual reset pins (MR1 and MR2)

 $\overline{\text{MR1}}$ and $\overline{\text{MR2}}$ are active low input terminals used to trigger a reset condition. When either $\overline{\text{MR1}}$ or $\overline{\text{MR2}}$ is pulled to logic low, a POR (RESET) occurs. These terminals have a 6-µA pullup current to V_{IN1}. It is recommended that these pins be pulled high to V_{IN} when they are not used.

sense (V_{SENSE1}, V_{SENSE2})

The sense terminals of fixed-output options must be connected to the regulator output, and the connection should be as short as possible. Internally, the sense terminals connect to high-impedance wide-bandwidth amplifiers through resistor-divider networks and noise pickup feeds through to the regulator output. It is essential to route the sense connections in such a way to minimize/avoid noise pickup. Adding RC networks between the V_{SENSE} terminals and V_{OUT} terminals to filter noise is not recommended because it can cause the regulators to oscillate.

RESET indicator

 $\label{eq:RESET} \hline RESET is an active low, open drain output and requires a pullup resistor for normal operation. When pulled up, RESET goes to a high impedance state (i.e. logic high) after a 120 ms delay when all three of the following conditions are met. First, V_{IN1} must be above the undervoltage condition. Second, the manual reset (MR) pin must be in a high impedance state. Third, V_{OUT2} must be above approximately 95% of its regulated voltage. To monitor V_{OUT1}, the PG1 output pin can be connected to MR1 or MR2.$

V_{IN1} and V_{IN2}

VIN1 and VIN2 are inputs to the regulators.

V_{OUT1} and V_{OUT2}

 V_{OUT1} and V_{OUT2} are output terminals of each regulator.



absolute maximum ratings over operating junction temperature (unless otherwise noted)[†]

| Input voltage range‡: V _{IN1} | –0.3 V to 7 V |
|---|--------------------|
| V _{IN2} | |
| Voltage range at EN | 0.3 V to 7 V |
| Output voltage range (V _{OUT1} , V _{SENSE1}) | |
| Output voltage range (V _{OUT2} , V _{SENSE2}) | |
| Maximum RESET, PG1 voltage | |
| Maximum MR1, MR2, and SEQ voltage | V _{IN1} |
| Peak output current | Internally limited |
| Operating virtual junction temperature range, T ₁ | |
| Storage temperature range, T _{stg} | –65°C to 150°C |
| ESD rating, HBM | |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

‡ All voltages are tied to network ground.

recommended operating conditions

| | MIN | MAX | UNIT |
|--|-----|-----|------|
| Input voltage, VI [¶] | 2.7 | 6 | V |
| Output current, I _O (regulator 1) | 0 | 1 | A |
| Output current, IO (regulator 2) | 0 | 2 | А |
| Operating virtual junction temperature, TJ | -55 | 125 | °C |

To calculate the minimum input voltage for maximum output current, use the following equation: VI(min) = VO(max) + VDO(max load).



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electrical characteristics over recommended operating junction temperature ($T_J = -55^{\circ}C$ to $125^{\circ}C$) V_{IN1} or V_{IN2} = V_{OUTX}(nom) + 1 V, I_{OUTX} = 1 mA, EN = 0, C_{OUT1} = 22 µF, C_{OUT2} = 47 µF(unless otherwise) noted)

| | PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT | |
|--|--|-----------------------------------|---|-------|-------|----------|------|--|
| | Output voltage | Reference voltage | 2.7 V < V _I < 6 V, FB connected to V _O T _J = 25°C | | 1.224 | | | |
| VO | (see Note 1 and | | $2.7 \text{ V} < \text{V}_{I} < 6 \text{ V}$, FB connected to V_{O} | 1.196 | | 1.248 | V | |
| Ũ | Note 3) | 1.2 V Output | 2.7 V < VI < 6 V, TJ = 25°C | | 1.2 | | | |
| | | (V _{OUT2}) | 2.7 V < V _I < 6 V | 1.176 | | 1.224 | | |
| Quiesce | Quiescent current (GND current) for regulator 1 and | | See Note 3, TJ = 25°C | | 185 | | ۸ | |
| regulato | regulator 2, $\overline{EN} = 0$ V, (see Note 1) | | See Note 3 | | | 250 | μA | |
| Output voltage line regulation ($\Delta V_O/V_O$) for regulator 1 and regulator 2 (see Note 2) | | for regulator | V_{O} + 1 V < $V_{I} \le 6$ V, T_{J} = 25°C, See Note 1 | | 0.01% | | v | |
| | | | V_{O} + 1 V < $V_{I} \le 6$ V, See Note 1 | | | 0.1% | V | |
| Load reg | gulation for V _{OUT1} and V _{OU} . | T2 | $T_J = 25^{\circ}C$, See Note 3 | | 1 | | mV | |
| Output current limit Regulator 1 Regulator 2 | | Regulator 1 | | | 1.75 | 2.35 | ^ | |
| | | Regulator 2 | $V_{O} = 0 V$ | | 3.8 | 4.8 | A | |
| Therma | I shutdown junction temperatu | ıre | | 150 | | | °C | |
| I _{l(standby)} Standby current | | | $EN = V_I, T_J = 25^{\circ}C$ | | 1 | 2 | | |
| | | | $EN = V_I$ | | | 10 | μA | |
| RESET | terminal | | | | | | | |
| Minimur | m input voltage for valid RESE | Т | I(RESET) = 300 μA, V(RESET) ≤ 0.8 V | | 1 | 1.3 | V | |
| Trip threshold voltage | | | V _O decreasing | 92% | 95% | 98% | VO | |
| Hystere | sis voltage | | Measured at V _O | | 0.5% | | VO | |
| t(RESE | T) | | RESET pulse duration | 80 | 120 | 160 | ms | |
| tr(RESE |) T) | | Rising edge deglitch | | 30 | | μs | |
| , | ow voltage | | VI = 3.5 V, I(RESET) = 1 mA | | 0.15 | 0.4 | V | |
| Leakage | e current | | V _(RESET) = 6 V | | | 1 | μA | |
| PG term | ninal | | () | | | | | |
| Minimur | m input voltage for valid PG | | I(PG) = 300 μA, V(PG1) ≤ 0.8 V | | 1.0 | 1.3 | V | |
| Trip thre | eshold voltage | | Vo decreasing | 92% | 95% | 98% | ٧o | |
| Hystere | sis voltage | | Measured at VO | | 0.5% | | Vo | |
| tr(PG1) | | | Rising edge deglitch | | 30 | | μs | |
| | ow voltage | | V _I = 2.7 V, I _(PG) = 1 mA | | 0.15 | 0.4 | V | |
| Leakage | e current | | V(PG1) = 6 V | | | 1 | μΑ | |
| EN term | | | · · · · | - | | · | | |
| High-lev | vel EN input voltage | | | 2 | | | V | |
| - | el EN input voltage | | | | | 0.7 | V | |
| Input cu | Irrent (EN) | | | -1 | | 1 | μA | |

NOTES: 1. Minimum input operating voltage is 2.7 V or VO(typ) + 1 V, whichever is greater. Maximum input voltage = 6 V, minimum output current is 1 mA.

2. If V_O < 1.8 V then V_{Imax} = 6 V, V_{Imin} = 2.7 V:

Line regulation (mV) =
$$(\%/V) \times \frac{V_O(V_{Imax} - 2.7 V)}{100} \times 1000$$

If
$$V_O > 2.5$$
 V then $V_{Imax} = 6$ V, $V_{Imin} = V_O + 1$ V:

Line regulation (mV) =
$$(\%/V) \times \frac{V_O(V_{Imax} - (V_O + 1))}{100} \times 1000$$

3. $I_O = 1 \text{ mA to } 1 \text{ A for regulator } 1 \text{ and } 1 \text{ mA to } 2 \text{ A for regulator } 2$.



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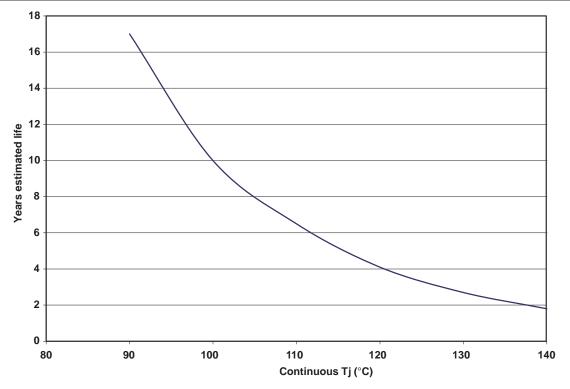
electrical characteristics over recommended operating junction temperature (T_J = -55°C to 125°C) V_{IN1} or $V_{IN2} = V_{OUTX(nom)} + 1 V$, $I_{OUTX} = 1 \text{ mA}$, EN = 0, $C_{OUT1} = 22 \,\mu\text{F}$, $C_{OUT2} = 47 \,\mu\text{F}$ (unless otherwise noted) (continued)

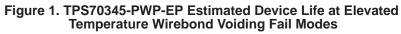
| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|-----------------------|-------------------|-----------|------|
| SEQ TERMINAL | - | | | | |
| High-level SEQ input voltage | | 2 | | | V |
| Low-level SEQ input voltage | | | | 0.7 | V |
| SEQ pullup current source | | | 6 | | μΑ |
| MR1 / MR2 TERMINALS | | | | | |
| High-level input voltage | | 2 | | | V |
| Low-level input voltage | | | | 0.7 | V |
| Pullup current source | | | 9.5 | | μΑ |
| V _{OUT2} TERMINAL | | | | | |
| V _{OUT2} UV comparator – positive-going input threshold voltage of V _{OUT1} UV comparator | | 80% V _O | 83% VO | 86% VO | V |
| VOUT2 UV comparator – hysteresis | | | 3% V _O | | mV |
| VOUT2 UV comparator – falling edge deglitch | VSENSE2 decreasing below threshold | | 140 | | μs |
| Peak output current | 2 ms pulse width | | 3 | | А |
| Discharge transistor current | V _{OUT2} = 1.5 V | | 7.5 | | mA |
| V _{OUT1} TERMINAL | | | | | |
| V _{OUT1} UV comparator – positive-going input threshold voltage of V _{OUT1} UV comparator | | 80% VO | 83% VO | 86% VO | V |
| VOUT1 UV comparator – hysteresis | | | 3% V _O | | mV |
| VOUT1 UV comparator – falling edge deglitch | VSENSE1 decreasing below threshold | | 140 | | μs |
| | I _O = 1 A, V _{IN1} = 3.2 V, T _J = 25°C | | 160 | | |
| Dropout voltage (see Note 4) | I _O = 1 A, V _{IN1} = 3.2 V | | | 255 | mV |
| Peak output current | 2 ms pulse width | | 1.2 | | А |
| Discharge transistor current | V _{OUT1} = 1.5 V | | 7.5 | | mA |
| VIN1 / VIN2 TERMINAL | | | | | |
| UVLO threshold | | 2.3 | | 2.65 | V |
| UVLO hysteresis | | | 110 | | mV |

NOTE 4: Input voltage(VIN1 or VIN2) = VO(Typ) - 100 mV. For the 1.5-V, 1.8-V and 2.5-V regulators, the dropout voltage is limited by input voltage range. The 3.3 V regulator input voltage is set to 3.2 V to perform this test.



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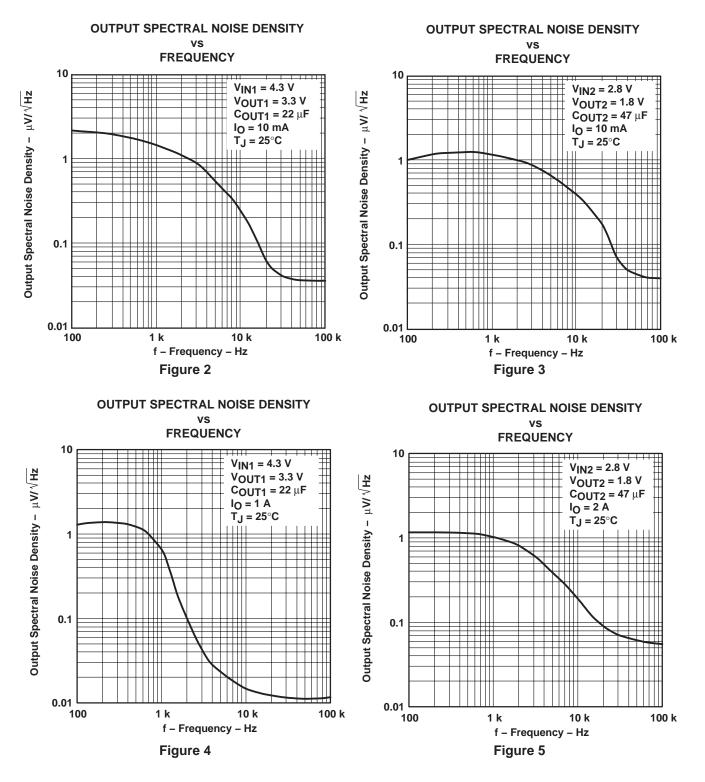
TYPICAL CHARACTERISTICS

Table of Graphs

| | | | FIGURE |
|----------------|-----------------------------------|--------------------|---------|
| | Output spectral noise density | vs Frequency | 2 – 5 |
| z ₀ | Output impedance | vs Frequency | 6 – 9 |
| | Load transient response | | 10, 11 |
| | Line transient response | | 12, 13 |
| VO | Output voltage and enable voltage | vs Time (start-up) | 14, 15 |
| | Equivalent series resistance | vs Output current | 16 – 20 |

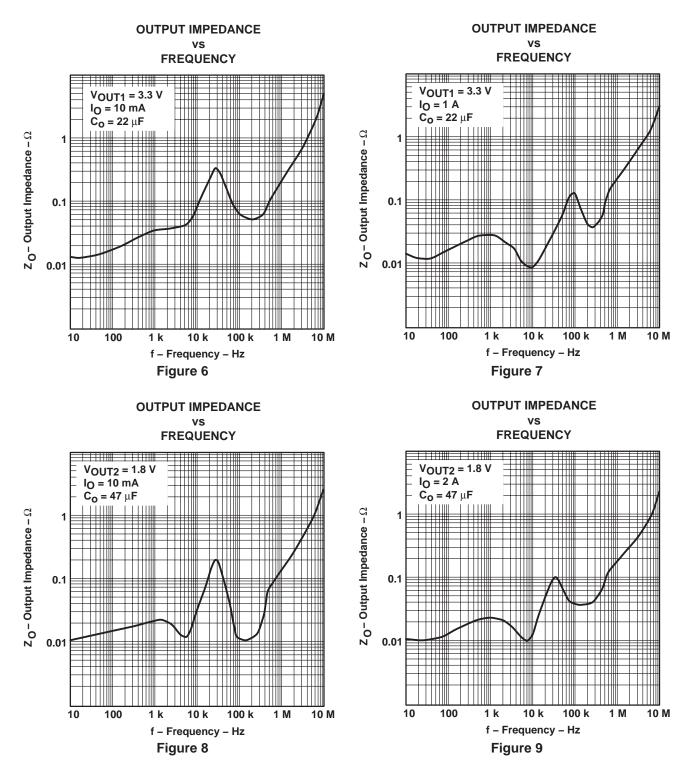


TYPICAL CHARACTERISTICS





TYPICAL CHARACTERISTICS





LOAD TRANSIENT RESPONSE LOAD TRANSIENT RESPONSE I_O – Output Current – A I_O - Output Current - A V_{IN1} = 4.3 V VOUT2 = 1.8 V V_{OUT1} = 3.3 V l_O = 2 A 1 2 $C_0 = 22 \ \mu F$ $C_0 = 47 \ \mu F$ Ŧ Tj = 25°C Tj = 25°C 0.5 1 + 0 0 +++ +++++++ ++++ ++++++++++ ++++ ++∓++++ 50 +++ ∆VO – Change in Output Voltage – mV ∆VO – Change in Output Voltage – mV 0 50 + 1 -50 0 -100 -50 0 0.2 0.4 0.6 0.8 1 1.2 1.4 1.6 1.8 0.2 0.4 0.6 0.8 1.4 1.6 1.8 2 0 1 1.2 2 t - Time - ms t – Time – ms Figure 10 Figure 11 LINE TRANSIENT RESPONSE LINE TRANSIENT RESPONSE V_I – Input Voltage – V V_I – Input Voltage – V V_{OUT1} = 3.3 V V_{OUT2} = 1.8 V I_O = 1 A 5.3 3.8 $I_0 = 2 A$ Co = 22 μF **C**₀ = 47 μF 4.3 2.8 ++++ +++ ∆VO - Change in Output Voltage - mV ∆VO – Change in Output Voltage – mV 50 100 0 0 -50 -100 -100 -200 20 40 100 120 140 160 180 200 60 80 0 20 40 60 100 120 140 160 180 200 0 80 t – Time – μ s t – Time – μs Figure 12 Figure 13

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

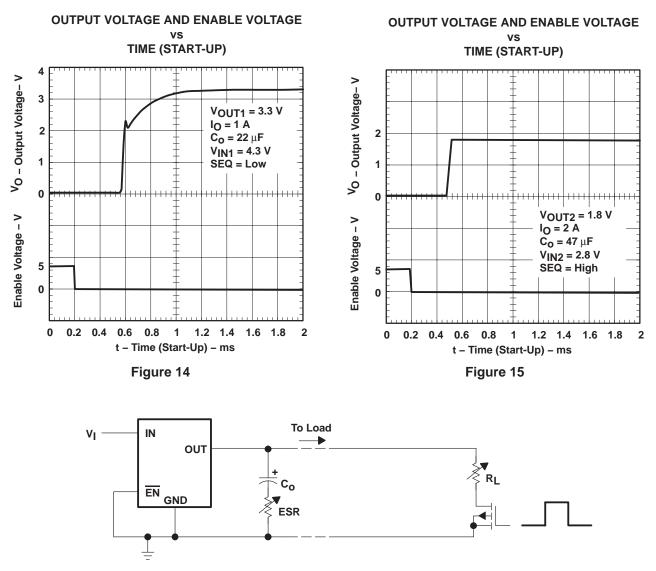
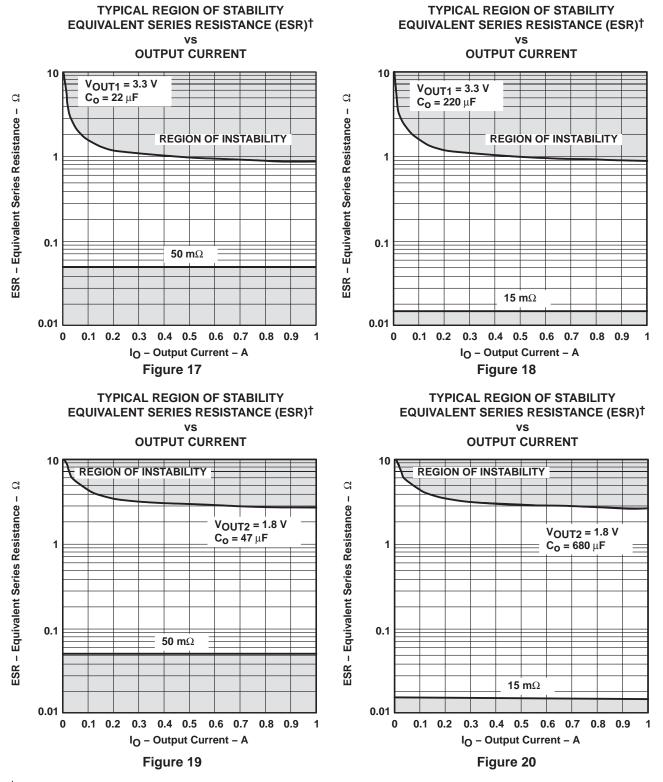


Figure 16. Test Circuit for Typical Regions of Stability

⁺ Equivalent series resistance (ESR) refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to C₀.







† Equivalent series resistance (ESR) refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to Co.



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THERMAL INFORMATION

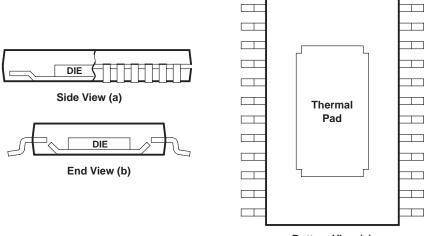
thermally enhanced TSSOP-24 (PWP – PowerPad™)

The thermally enhanced PWP package is based on the 24-pin TSSOP, but includes a thermal pad (see Figure 21(c)] to provide an effective thermal contact between the IC and the PWB.

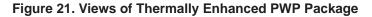
Traditionally, surface mount and power have been mutually exclusive terms. A variety of scaled-down TO220-type packages have leads formed as gull wings to make them applicable for surface-mount applications. These packages, however, suffer from several shortcomings: they do not address the low profile requirements (<2 mm) of many of today's advanced systems, and they do not offer a pin-count high enough to accommodate increasing integration. On the other hand, traditional low-power surface-mount packages require power-dissipation derating that severely limits the usable range of many high-performance analog circuits.

The PWP package (thermally enhanced TSSOP) combines fine-pitch surface-mount technology with thermal performance comparable to much larger power packages.

The PWP package is designed to optimize the heat transfer to the PWB. Because of the small size and limited mass of a TSSOP package, thermal enhancement is achieved by improving the thermal conduction paths that remove heat from the component. The thermal pad is formed using a lead-frame design (patent pending) and manufacturing technique to provide the user with direct connection to the heat-generating IC. When this pad is soldered or otherwise coupled to an external heat dissipator, high power dissipation in the ultrathin, fine-pitch, surface-mount package can be reliably achieved.



Bottom View (c)



Because the conduction path has been enhanced, power-dissipation capability is determined by the thermal considerations in the PWB design. For example, simply adding a localized copper plane (heat-sink surface), which is coupled to the thermal pad, enables the PWP package to dissipate 2.5 W in free air (reference Figure 23(a), 8 cm² of copper heat sink and natural convection). Increasing the heat-sink size increases the power dissipation range for the component. The power dissipation limit can be further improved by adding airflow to a PWB/IC assembly (see Figure 22 and Figure 23). The line drawn at 0.3 cm² in Figure 22 and Figure 23 indicates performance at the minimum recommended heat-sink size, illustrated in Figure 24.



THERMAL INFORMATION

thermally enhanced TSSOP-24 (PWP – PowerPad[™]) (continued)

The thermal pad is directly connected to the substrate of the IC, which for the TPS70345 series is a secondary electrical connection to device ground. The heat-sink surface that is added to the PWP can be a ground plane or left electrically isolated. In TO220-type surface-mount packages, the thermal connection is also the primary electrical connection for a given terminal which is not always ground. The PWP package provides up to 24 independent leads that can be used as inputs and outputs (Note: leads 1, 12, 13, and 24 are internally connected to the thermal pad and the IC substrate).

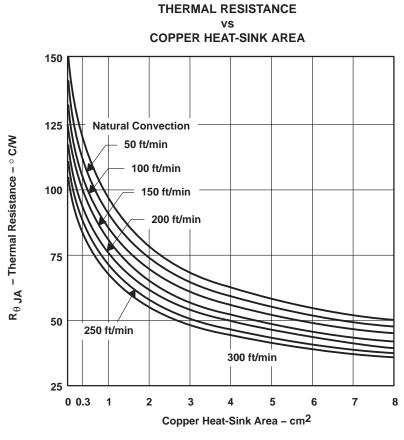
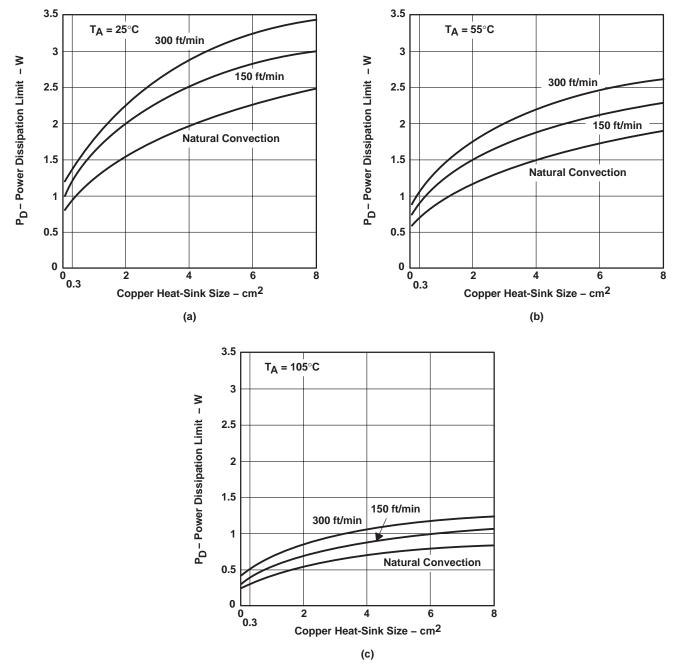


Figure 22



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THERMAL INFORMATION



thermally enhanced TSSOP-24 (PWP – PowerPad[™]) (continued)

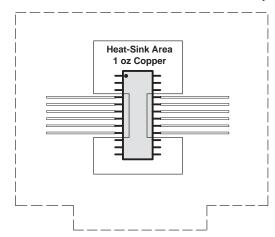
Figure 23. Power Ratings of the PWP Package at Ambient Temperatures of 25°C, 55°C, and 105°C



THERMAL INFORMATION

thermally enhanced TSSOP-24 (PWP – PowerPad[™]) (continued)

Figure 24 is an example of a thermally enhanced PWB layout for use with the new PWP package. This board configuration was used in the thermal experiments that generated the power ratings shown in Figure 22 and Figure 23. As discussed earlier, copper has been added on the PWB to conduct heat away from the device. $R_{\theta JA}$ for this assembly is illustrated in Figure 22 as a function of heat-sink area. A family of curves is included to illustrate the effect of airflow introduced into the system.



| Board thickness | 62 mils |
|------------------------|-----------------------|
| Board size | 3.2 in. × 3.2 in. |
| Board material | FR4 |
| Copper trace/heat sink | 1 oz |
| Exposed pad mounting | 63/67 tin/lead solder |

Figure 24. PWB Layout (Including Copper Heatsink Area) for Thermally Enhanced PWP Package

From Figure 22, $R_{\theta JA}$ for a PWB assembly can be determined and used to calculate the maximum power-dissipation limit for the component/PWB assembly, with the equation:

$$P_{D(max)} = \frac{T_J max - T_A}{R_{\theta JA(system)}}$$
(1)

where

 T_J max is the maximum specified junction temperature (150°C absolute maximum limit, 125°C recommended operating limit) and T_A is the ambient temperature.

P_{D(max)} should then be applied to the internal power dissipated by the TPS70345 regulator. The equation for calculating total internal power dissipation of the TPS70345 is:

$$\mathsf{P}_{\mathsf{D}(\mathsf{total})} = \left(\mathsf{V}_{\mathsf{IN1}} - \mathsf{V}_{\mathsf{OUT1}}\right) \times \mathsf{I}_{\mathsf{OUT1}} + \mathsf{V}_{\mathsf{IN1}} \times \frac{\mathsf{I}_{\mathsf{Q}}}{2} + \left(\mathsf{V}_{\mathsf{IN2}} - \mathsf{V}_{\mathsf{OUT2}}\right) \times \mathsf{I}_{\mathsf{OUT2}} + \mathsf{V}_{\mathsf{IN2}} \times \frac{\mathsf{I}_{\mathsf{Q}}}{2}$$
(2)

Since the quiescent current of the TPS703xx is low, the second term is negligible, further simplifying the equation to:

$$\mathsf{P}_{\mathsf{D}(\mathsf{total})} = \left(\mathsf{V}_{\mathsf{IN1}} - \mathsf{V}_{\mathsf{OUT1}}\right) \times \mathsf{I}_{\mathsf{OUT1}} + \left(\mathsf{V}_{\mathsf{IN2}} - \mathsf{V}_{\mathsf{OUT2}}\right) \times \mathsf{I}_{\mathsf{OUT2}}$$
(3)

For the case where $T_A = 55^{\circ}C$, airflow = 200 ft/min, copper heat-sink area = 4 cm², the maximum power-dissipation limit can be calculated. First, from Figure 22, we find the system $R_{\theta JA}$ is 50°C/W; therefore, the maximum power-dissipation limit is:

$$P_{D(max)} = \frac{T_{J}max - T_{A}}{R_{\theta JA(system)}} = \frac{125 \,^{\circ} C - 55 \,^{\circ} C}{TBD \,^{\circ} C/W} = TBD \,^{\circ} W$$
(4)



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THERMAL INFORMATION

thermally enhanced TSSOP-24 (PWP – PowerPad[™]) (continued)

If the system implements a TPS70345 regulator, where $V_I = 5 V$ and $I_O = 800 \text{ mA}$, the internal power dissipation is:

$$P_{D(\text{total})} = (V_{\text{IN1}} - V_{\text{OUT1}}) \times I_{\text{OUT1}} + (V_{\text{IN2}} - V_{\text{OUT2}}) \times I_{\text{OUT2}}$$

$$= (4.3 - 3.3) \times 0.8 + (2.8 - 1.8) \times 1 = -1.8 \text{ W}$$
(5)

Comparing PD(total) with PD(max) reveals that the power dissipation in this example does not exceed the calculated limit. When it does, one of two corrective actions should be made: raising the power-dissipation limit by increasing the airflow or the heat-sink area, or lowering the internal power dissipation of the regulator by reducing the input voltage or the load current. In either case, the above calculations should be repeated with the new system parameters. This parameter is measured with the recommended copper heat sink pattern on a 4-layer PCB, 2 oz. copper traces on 4-in \times 4-in ground layer. Simultaneous and continuous operation of both regulator outputs at full load may exceed the power dissipation rating of the PWP package.

mounting information

The primary requirement is to complete the thermal contact between the thermal pad and the PWB metal. The thermal pad is a solderable surface and is fully intended to be soldered at the time the component is mounted. Although voiding in the thermal-pad solder-connection is not desirable, up to 50% voiding is acceptable. The data included in Figure 22 and Figure 23 is for soldered connections with voiding between 20% and 50%. The thermal analysis shows no significant difference resulting from the variation in voiding percentage.

Figure 25 shows the solder-mask land pattern for the PWP package. The minimum recommended heat-sink area is also illustrated. This is simply a copper plane under the body extent of the package, including metal routed under terminals 1, 12, 13, and 24.

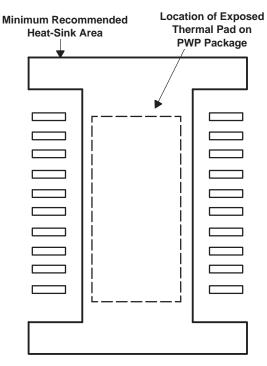


Figure 25. PWP Package Land Pattern



APPLICATION INFORMATION

sequencing timing diagrams

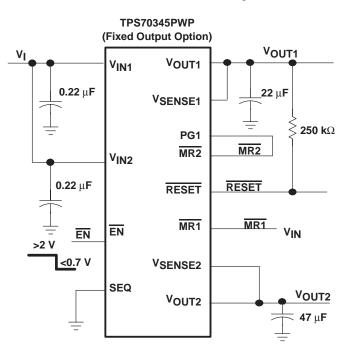
The following figures provide a timing diagram of how this device functions in different configurations.

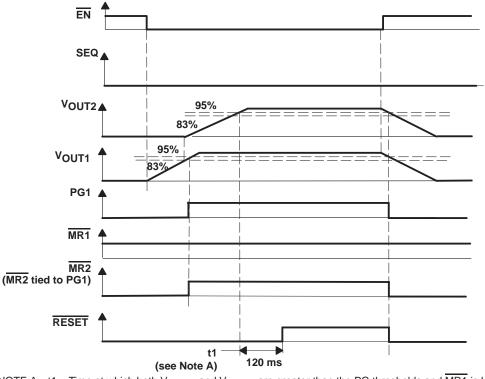
application conditions not shown in block diagram:

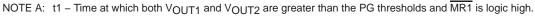
 V_{IN1} and V_{IN2} are tied to the same fixed input voltage greater than the V_{UVLO} ; SEQ is tied to logic low; PG1 is tied to MR2; MR1 is not used and is connected to V_{IN} .

explanation of timing diagrams:

EN is initially high; therefore, both regulators are off and PG1 and RESET are at logic low. With SEQ at logic low, when EN is taken to logic low, V_{OUT1} turns on. V_{OUT2} turns on after V_{OUT1} reaches 83% of its regulated output voltage. When V_{OUT1} reaches 95% of its regulated output voltage, PG1 (tied to MR2) goes to logic high. When both V_{OUT1} and V_{OUT2} reach 95% of their respective regulated output voltages and both MR1 and MR2 (tied to PG1) are at logic high, RESET is pulled to logic high after a 120 ms delay. When EN is returned to logic high, both devices power down and both PG1 (tied to MR2) and RESET return to logic low.











APPLICATION INFORMATION

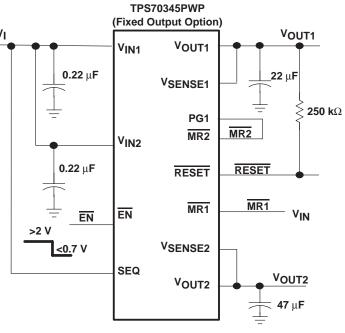
sequencing timing diagrams (continued)

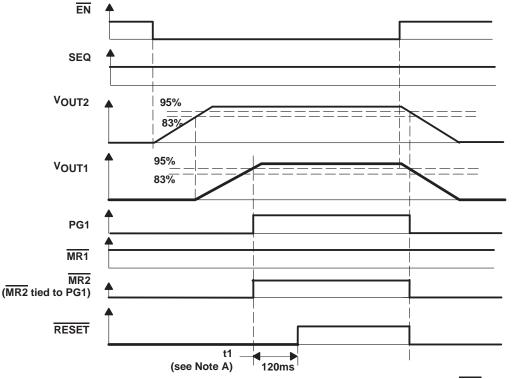
application conditions not shown in block diagram:VI

 V_{IN1} and V_{IN2} are tied to the same fixed input voltage greater than the V_{UVLO} ; SEQ is tied to logic high; PG1 is tied to MR2; MR1 is not used and is connected to V_{IN} .

explanation of timing diagrams:

 $\overline{\text{EN}}$ is initially high; therefore, both regulators are off and PG1 and RESET are at logic low. With SEQ at logic high, when $\overline{\text{EN}}$ is taken to logic low, V_{OUT2} turns on. V_{OUT1} turns on after V_{OUT2} reaches 83% of its regulated output voltage. When V_{OUT1} reaches 95% of its regulated output voltage, PG1 (tied to $\overline{\text{MR2}}$) goes to logic high. When both V_{OUT1} and V_{OUT2} reach 95% of their respective regulated output voltages and both $\overline{\text{MR1}}$ and $\overline{\text{MR2}}$ (tied to PG1) are at logic high, RESET is pulled to logic high after a 120 ms delay. When $\overline{\text{EN}}$ is returned to logic high, both devices turn off and both PG1 (tied to $\overline{\text{MR2}}$) and $\overline{\text{RESET}}$ return to logic low.





NOTE A: t1 – Time at which both V_{OUT1} and V_{OUT2} are greater than the PG thresholds and MR1 is logic high.

Figure 27. Timing When SEQ = High



APPLICATION INFORMATION

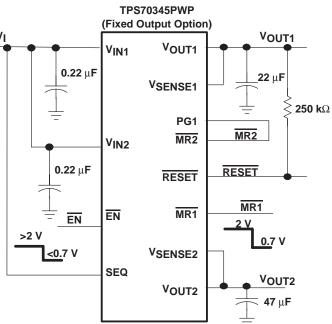
sequencing timing diagrams (continued)

application conditions not shown in block diagram: VI

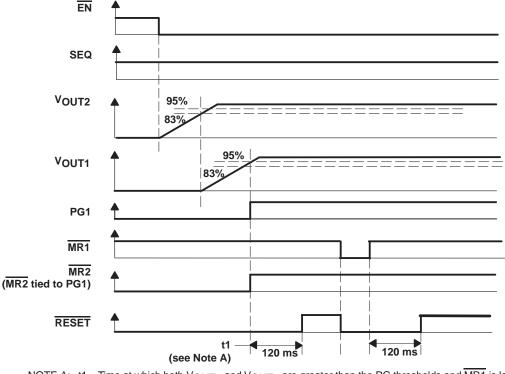
 V_{IN1} and V_{IN2} are tied to the same fixed input voltage greater than the V_{UVLO} ; SEQ is tied to logic high; PG1 is tied to MR2; MR1 is initially at logic high but is eventually toggled.

explanation of timing diagrams:

 $\overline{\rm EN}$ is initially high; therefore, both regulators are off and PG1 and $\overline{\rm RESET}$ are at logic low. With SEQ at logic high, when $\overline{\rm EN}$ is taken low, V_{OUT2} turns on. V_{OUT1} turns on after V_{OUT2} reaches 83% of its regulated output voltage. When V_{OUT1} reaches 95% of its regulated output voltage, PG1 (tied to $\overline{\rm MR2}$) goes to logic high. When both V_{OUT1} and V_{OUT2} reach 95% of their respective regulated output voltages and both $\overline{\rm MR1}$ and $\overline{\rm MR2}$ (tied to PG1) are at logic high, $\overline{\rm RESET}$ is pulled to logic high after a 120 ms delay. When $\overline{\rm MR1}$ is taken low, $\overline{\rm RESET}$ returns to logic low but the



outputs remain in regulation. When $\overline{\text{MR1}}$ is returned to logic high, since both V_{OUT1} and V_{OUT2} remain above 95% of their respective regulated output voltages and $\overline{\text{MR2}}$ (tied to PG1) remains at logic high, RESET is pulled to logic high after a 120 ms delay.



NOTE A: t1 – Time at which both V_{OUT1} and V_{OUT2} are greater than the PG thresholds and MR1 is logic high.

Figure 28. Timing When MR1 Is Toggled



APPLICATION INFORMATION

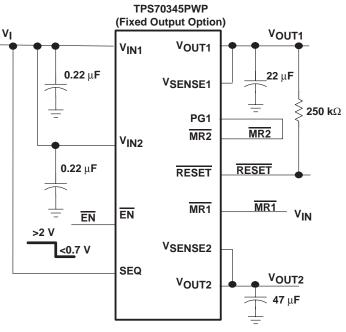
sequencing timing diagrams (continued)

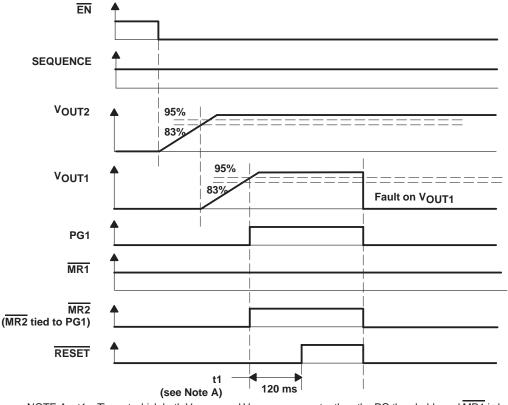
application conditions not shown in block diagram: Vi

 V_{IN1} and V_{IN2} are tied to the same fixed input voltage greater than the $V_{UVLO};\ SEQ$ is tied to logic high; PG1 is tied to MR2; MR1 is not used and is connected to $V_{IN}.$

explanation of timing diagrams:

 $\overline{\rm EN}$ is initially high; therefore, both regulators are off and PG1 and $\overline{\rm RESET}$ are at logic low. With SEQ at logic high, when $\overline{\rm EN}$ is taken low, V_{OUT2} turns on. V_{OUT1} turns on after V_{OUT2} reaches 83% of its regulated output voltage. When V_{OUT1} reaches 95% of its regulated output voltage, PG1 (tied to $\overline{\rm MR2}$) goes to logic high. When both V_{OUT1} and V_{OUT2} reach 95% of their respective regulated output voltages and both $\overline{\rm MR1}$ and $\overline{\rm MR2}$ (tied to PG1) are at logic high, $\overline{\rm RESET}$ is pulled to logic high after a 120 ms delay. When a fault on V_{OUT1} causes it to fall below 95% of its regulated output voltage, PG1 (tied to $\overline{\rm MR2}$) goes to logic low.





NOTE A: t1 – Time at which both V_{OUT1} and V_{OUT2} are greater than the PG thresholds and MR1 is logic high.

Figure 29. Timing When a Fault Occurs on VOUT1



APPLICATION INFORMATION

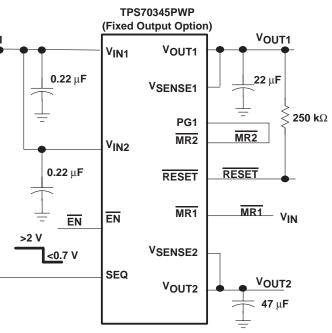
sequencing timing diagrams (continued)

application conditions not shown in block diagram: VI

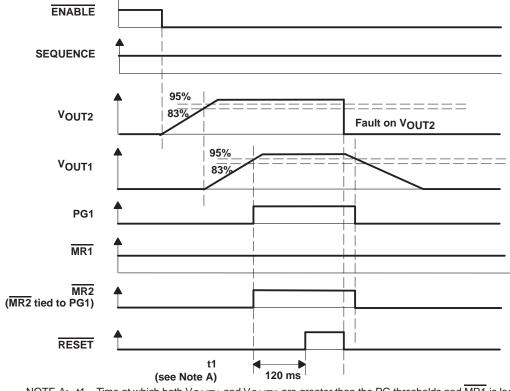
 V_{IN1} and V_{IN2} are tied to the same fixed input voltage greater than the V_{UVLO} ; SEQ is tied to logic high; PG1 is tied to MR2; MR1 is not used and is connected to V_{IN} .

explanation of timing diagrams:

 $\overline{\rm EN}$ is initially high; therefore, both regulators are off and PG1 and $\overline{\rm RESET}$ are at logic low. With SEQ at logic high, when $\overline{\rm EN}$ is taken low, V_{OUT2} turns on. V_{OUT1} turns on after V_{OUT2} reaches 83% of its regulated output voltage. When V_{OUT1} reaches 95% of its regulated output voltage, PG1 (tied to $\overline{\rm MR2}$) goes to logic high. When both V_{OUT1} and V_{OUT2} reach 95% of their respective regulated output voltages and both $\overline{\rm MR1}$ and $\overline{\rm MR2}$ (tied to PG1) are at logic high, $\overline{\rm RESET}$ is pulled to logic high after a 120 ms delay. When a fault on V_{OUT2} causes it to fall below 95% of its regulated



output voltage, RESET returns to logic low and V_{OUT1} begins to power down because SEQ is high. When V_{OUT1} falls below 95% of its regulated output voltage, PG1 (tied to MR2) returns to logic low.



NOTE A: t1 – Time at which both VOUT1 and VOUT2 are greater than the PG thresholds and MR1 is logic high.

Figure 30. Timing When a Fault Occurs on VOUT2



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APPLICATION INFORMATION

input capacitor

For a typical application, a ceramic input bypass capacitor ($0.22 \,\mu\text{F} - 1 \,\mu\text{F}$) is recommended to ensure device stability. This capacitor should be as close as possible to the input pin. Due to the impedance of the input supply, large transient currents causes the input voltage to droop. If this droop causes the input voltage to drop below the UVLO threshold, the device turns off. Therefore, it is recommended that a larger capacitor be placed in parallel with the ceramic bypass capacitor at the regulator's input. The size of this capacitor depends on the output current, response time of the main power supply, and the main power supply's distance to the regulator. At a minimum, the capacitor should be sized to ensure that the input voltage does not drop below the minimum UVLO threshold voltage during normal operating conditions.

output capacitor

As with most LDO regulators, the TPS70345 requires an output capacitor connected between each OUT and GND to stabilize the internal control loop. The minimum recommended capacitance value for V_{OUT1} is 22 μ F and the ESR (equivalent series resistance) must be between 50 m Ω and 800 m Ω . The minimum recommended capacitance value for V_{OUT2} is 47 μ F and the ESR must be between 50 m Ω and 2 Ω . Solid tantalum electrolytic, aluminum electrolytic, and multilayer ceramic capacitors are all suitable, provided they meet the requirements described above. Larger capacitors provide a wider range of stability and better load transient response. Below is a partial listing of surface-mount capacitors usable with the TPS70345 for fast transient response application.

This information, along with the ESR graphs, is included to assist in selection of suitable capacitance for the user's application. When necessary to achieve low height requirements along with high output current and/or high load capacitance, several higher ESR capacitors can be used in parallel to meet the guidelines above.

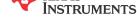
| VALUE | MFR. | PART NO. |
|--------|-------|----------------|
| 680 µF | Kemet | T510X6871004AS |
| 470 μF | Sanyo | 4TPB470M |
| 150 μF | Sanyo | 4TPC150M |
| 220 µF | Sanyo | 2R5TPC220M |
| 100 μF | Sanyo | 6TPC100M |
| 68 µF | Sanyo | 10TPC68M |
| 68 µF | Kemet | T495D6861006AS |
| 47 μF | Kemet | T495D4761010AS |
| 33 µF | Kemet | T495C3361016AS |
| 22 µF | Kemet | T495C2261010AS |

regulator protection

Both TPS70345 PMOS-pass transistors have built-in back diodes that conduct reverse currents when the input voltage drops below the output voltage (e.g., during power down). Current is conducted from the output to the input and is not internally limited. When extended reverse voltage is anticipated, external limiting may be appropriate.

The TPS70345 also features internal current limiting and thermal protection. During normal operation, the TPS70345 regulator 1 limits output current to approximately 1.75 A (typ) and regulator 2 limits output current to approximately 3.8 A (typ). When current limiting engages, the output voltage scales back linearly until the overcurrent condition ends. While current limiting is designed to prevent gross device failure, care should be taken not to exceed the power dissipation ratings of the package. If the temperature of the device exceeds 150°C(typ), thermal-protection circuitry shuts it down. Once the device has cooled below 130°C(typ), regulator operation resumes.





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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



| *All dimensions are nominal | |
|-----------------------------|--|
| | |
| | |

| Device | Package Type | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|-----------------|-----------------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| TPS70345MPWPREP | HTSSOP | PWP | 24 | 2000 | 330.0 | 16.4 | 6.95 | 8.3 | 1.6 | 8.0 | 16.0 | Q1 |



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PACKAGE MATERIALS INFORMATION

5-Dec-2023



*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|-----------------|--------------|-----------------|------|------|-------------|------------|-------------|
| TPS70345MPWPREP | HTSSOP | PWP | 24 | 2000 | 350.0 | 350.0 | 43.0 |

PWP 24

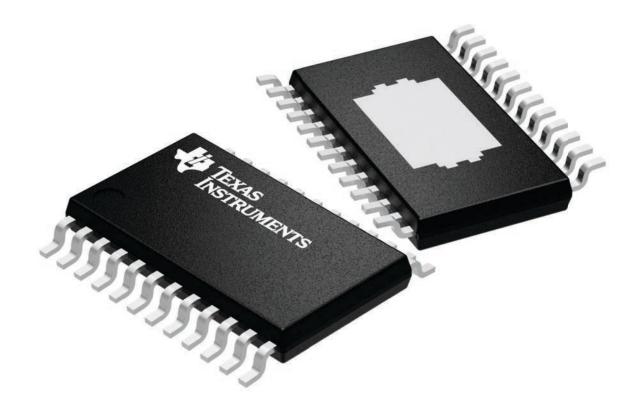
GENERIC PACKAGE VIEW

PowerPAD[™] TSSOP - 1.2 mm max height

PLASTIC SMALL OUTLINE

4.4 x 7.6, 0.65 mm pitch

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PWP (R-PDSO-G24)

PowerPAD[™] PLASTIC SMALL OUTLINE



All linear dimensions are in millimeters. NOTES: Α.

- Β. This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side. C.
- This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad D. Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com http://www.ti.com. E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.

E. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.



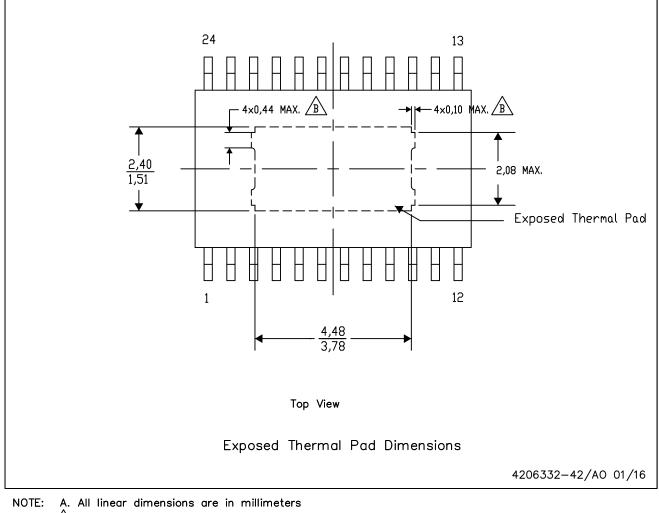
PWP (R-PDSO-G24) PowerPAD[™] SMALL PLASTIC OUTLINE

THERMAL INFORMATION

This PowerPAD[™] package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



/B. Exposed tie strap features may not be present.

PowerPAD is a trademark of Texas Instruments



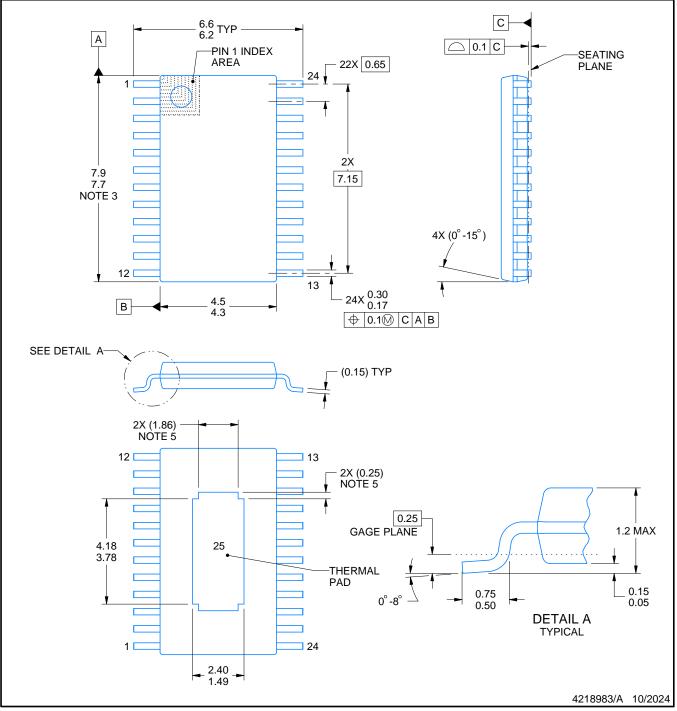
PWP0024A



PACKAGE OUTLINE

PowerPAD[™] TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not

- exceed 0.15 mm per side. 4. Reference JEDEC registration MO-153.
- 5. Features may differ or may not be present.

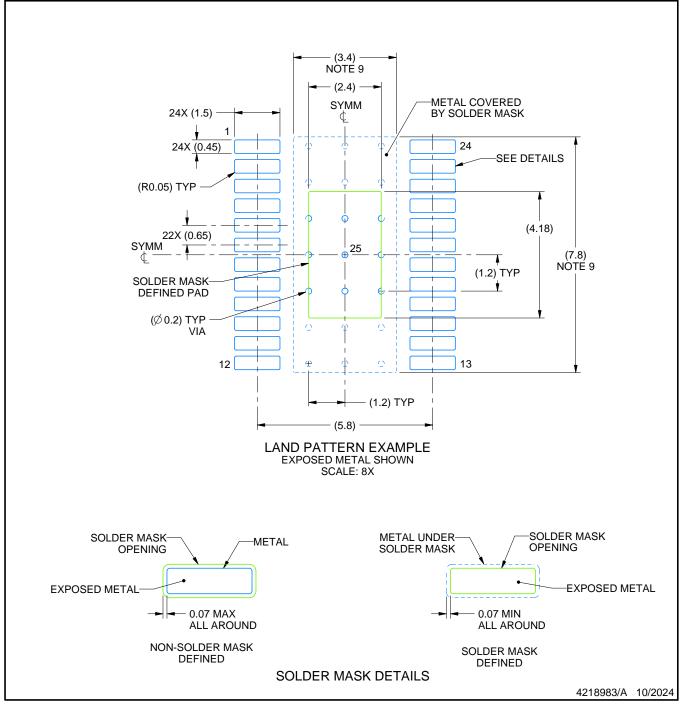


PWP0024A

EXAMPLE BOARD LAYOUT

PowerPAD[™] TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
- 9. Size of metal pad may vary due to creepage requirement.
- 10. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.

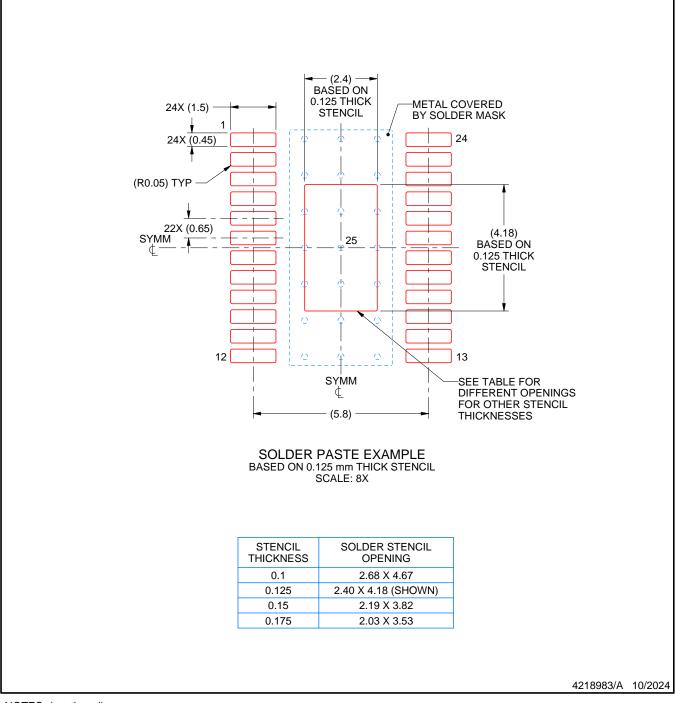


PWP0024A

EXAMPLE STENCIL DESIGN

PowerPAD[™] TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

12. Board assembly site may have different recommendations for stencil design.



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